



#19/Amdt C
6.23.03
C. Moore

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IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
AKIRA NISHIYAMA, ET AL. : EXAMINER: MAI, A.
SERIAL NO: 09/891,129 :
RCE FILED: HERewith : GROUP ART UNIT: 2814
FOR: SEMICONDUCTOR DEVICE :
HAVING AN INSULATING FILM
MADE OF A HIGHLY DIELECTRIC
THIN FILM AND METHOD OF
MANUFACTURING THE SAME

RECEIVED
JUN 11 2003
TECHNOLOGY CENTER 2800

AMENDMENT FILED CONCURRENTLY WITH
REQUEST FOR CONTINUED EXAMINATION (RCE)

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Prior to a further examination on the merits, please amend the above-identified application as follows:

IN THE CLAIMS

Please amend claims 1 and 16 to read as follows:¹

1. (Twice Amended) A semiconductor device comprising:

a semiconductor substrate, and

a circuit element using an insulating film formed on said semiconductor substrate,

said insulating film containing a silicon compound containing oxygen, and a metal

compound containing a metal other than silicon and oxygen, said insulating film further